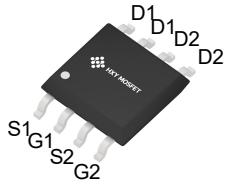
SI9926CDY-T1-GE3

Dual N-Channel Enhancement Mode MOSFET

Description

The SI9926CDY-T1-GE3 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

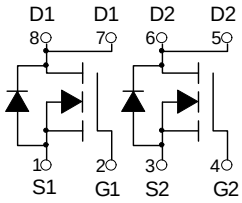


SOP-8
(SOIC-8)

General Features

V_{DS} = 20V I_D =8 A

$R_{DS(ON)}$ < 20mΩ @ V_{GS}=4.5V



Dual N-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SI9926CDY-T1-GE3	SOP-8(SOIC-8)	HXY MOSFET	3000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	±12	V
I_D	Drain Current-Continuous	8	A
I_{DM}	Pulsed Drain Current	28	A
P_D	Maximum Power Dissipation	2.25	W
T_J,T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	℃
$R_{\theta JC}$	Thermal Resistance,Junction-to-Case(Note 2)	80	℃/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0V, I_D = 250μA	20	-	-	V
Gate Leakage Current	I_{GSS}	V_{GS} = ±12V, V_{DS} = 0V	-	-	±100	nA
Drain Cut-off Current	I_{DSS}	V_{DS} = 20V, V_{GS} = 0V	-	-	1	μA
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS} = V_{DS}, I_D = 250μA	0.45	0.7	1	V
Drain-Source On-State Resistance[3]	$R_{DS(on)}$	V_{GS} = 4.5V, I_D =5A	-	13	20	mΩ
		V_{GS} = 2.5V, I_D = 4.7A	-	18	30	
		V_{GS} = 1.8V, I_D = 4.3A	-	28	57	
Dynamic Characteristics[4]						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 10V, f = 1MHz	-	700	-	pF
Output Capacitance	C_{oss}		-	120	-	
Reverse Transfer Capacitance	C_{rss}		-	105	-	
Switching Characteristics[4]						
Total Gate Charge	Q_g	V_{GS}= 4.5V, V_{DS}= 10V, I_D= 5A	-	10.5	-	nC
Gate-Source Charge	Q_{gs}		-	2	-	
Gate-Drain Charge	Q_{gd}		-	2.5	-	
Turn-On Time	$t_{d(on)}$	V_{GS}= 5V, V_{DD} = 10V, I_D = 5A,R_G= 3Ω,	-	10	-	ns
Rise Time	t_r		-	20	-	
Turn-Off Time	$t_{d(off)}$		-	32	-	
Fall Time	t_f		-	12	-	
Source-Drain Diode Characteristics						
Body Diode Voltage[3]	V_{SD}	I_S=4A, V_{GS} = 0V	-	-	1.2	V
Continuous Source Current	I_S		-	-	8	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C.
2. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width≤300μs, duty cycle≤2%.
4. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

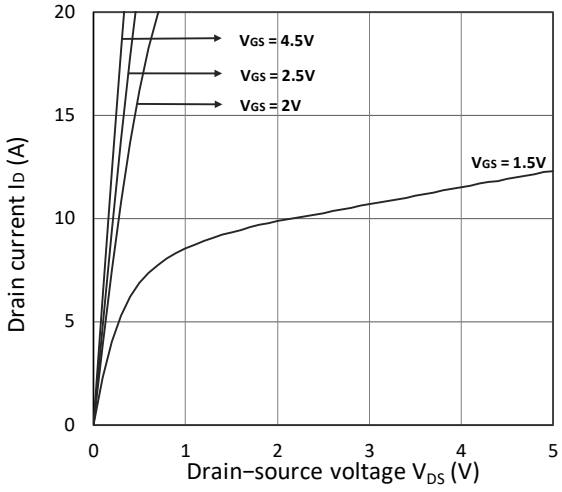


Figure 1. Output Characteristics

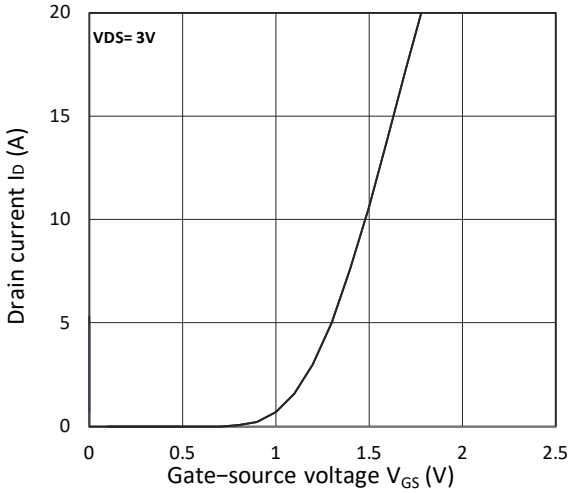


Figure 2. Transfer Characteristics

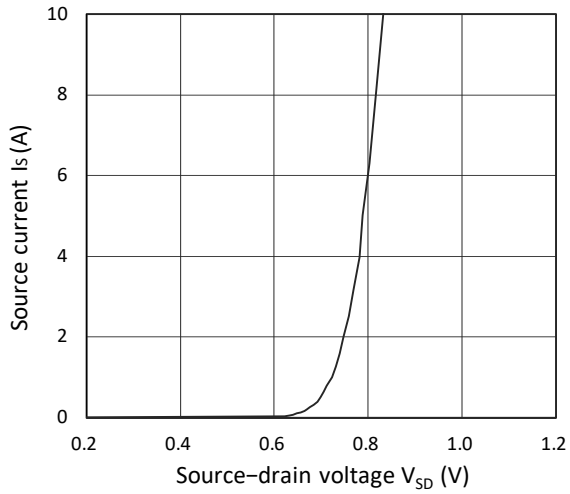


Figure 3. Forward Characteristics of Reverse

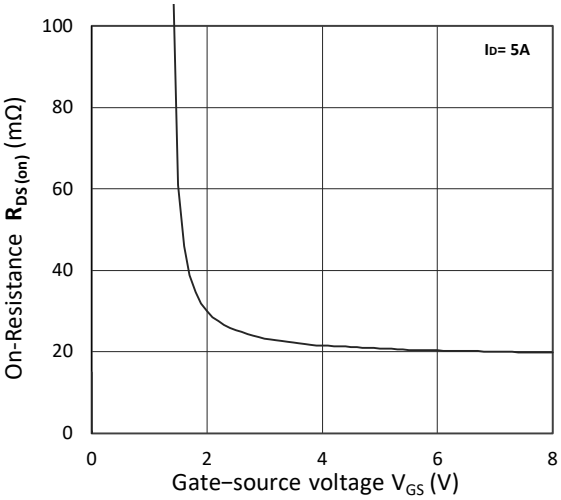


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

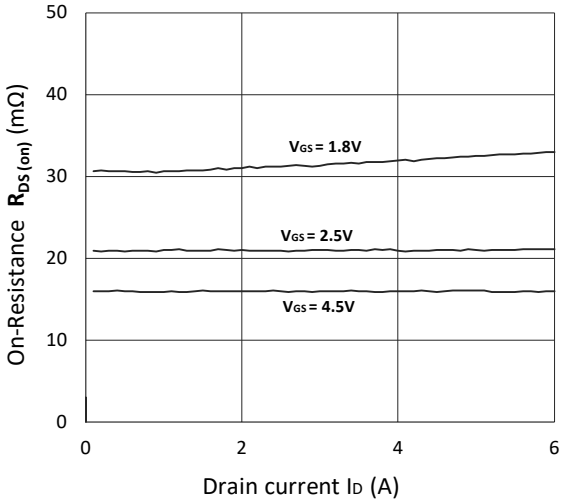


Figure 5. $R_{DS(ON)}$ vs. I_D

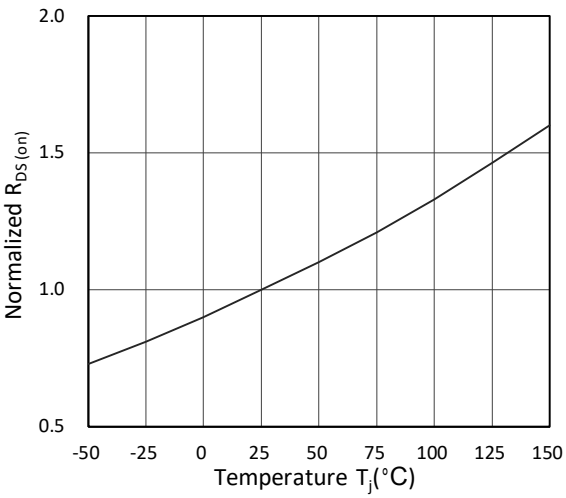


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

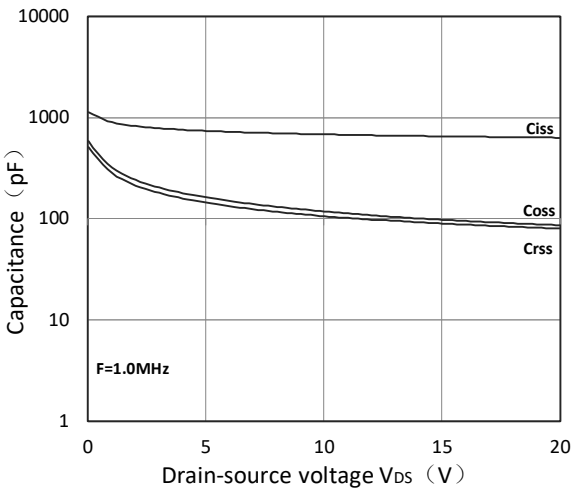


Figure 7. Capacitance Characteristics

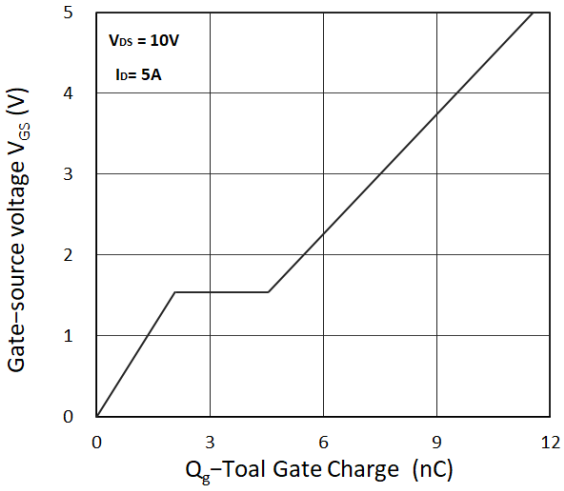
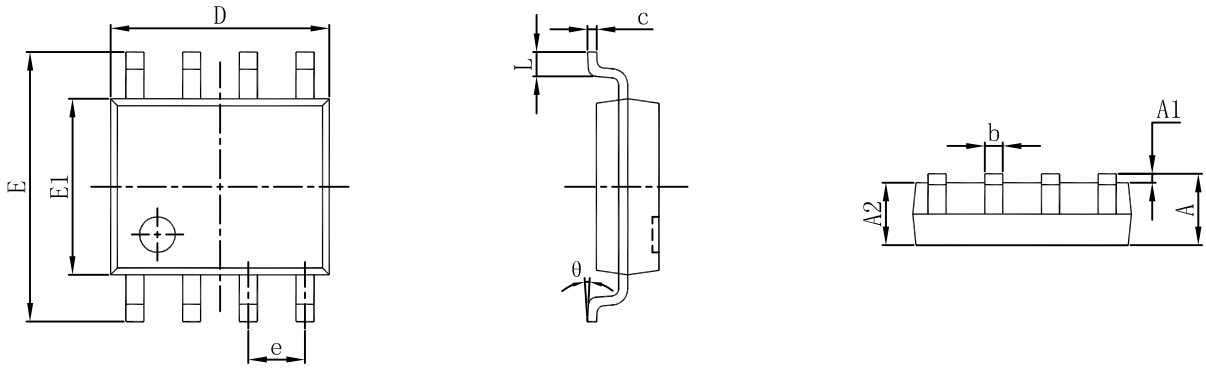
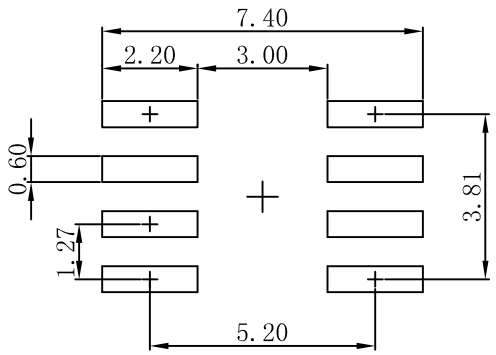


Figure 8. Gate Charge Characteristics

SOP-8(SOIC-8)Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	**Max**	**Min**	**Max**
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

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